DECLARATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF

: Kenji Todori et al.

SERIAL NUMBER

: 09/819,621

FOR

: OPTICAL DISK HAVING SUPER-

RESOLUTION FILM

FILED

: Maréh 29, 2001

GROUP ART UNIT

1756

EXAMINER

. Angebranndt, Martin J.

DECLARATION UNDER 37 C.F.R. 1.132

Assistant Commissioner for patents Washington, D.C. 20231

Sir

I. Kenii Todori, a co-applicant of the above-identified application, a national of Japan, declare as follows.

Sample 2A of Table 2 is compared with Samples 2B, 2C and 2D of Table 2.

Although it is clear that the absorption saturation characteristics (transmittance T under the power density of 1MW/cm²) of Sample 2A is superior to those of Samples 2B and 2D, it is equal to that of Sample 2C. However, the wavelength of light used for measurement of Sample 2A is different from that of Sample 2C. Therefore, Samples 2A and 2C are different in the effect as follows.

Equation (I) on page 30 of the specification is referred to.

$$\chi^{(3)} = \frac{-N\mu^4}{\omega - \omega_0 + i\Gamma} \left[\frac{2\Gamma}{\gamma} \frac{1}{(\omega_0 - \omega)^2 + \Gamma^2} + \frac{2}{i\gamma} \left(\frac{1}{\omega_0 - \omega_1 - i\Gamma} + \frac{-1}{\omega_0 - \omega_1 + i\Gamma} \right) \right]$$
... (1)

The absorption saturation phenomenon has a positive correlation with the third-order nonlinear optical constant $\chi^{(3)}$. The energy relaxation constant y in the Equation (I) can be regarded as being the same as the transition probability A_{ab} (Einstein's A coefficient) of spontaneous emission.

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The transition probability A_{ab} is represented by the following equation.

$$A_{ab} = \frac{2\pi}{\hbar^2} \frac{\hbar}{2\epsilon_a V} \frac{V}{\pi^3 c^3} \int d\omega_\lambda \frac{{\omega_\lambda}^2}{\omega_a} \, {\omega_{b_a}}^2 \, \frac{1}{3} \left| P_{ab} \right|^2 \delta(\omega_\lambda - \omega_{ba}) = \frac{{\omega_{ba}}^3}{3\pi_0 \epsilon_0 \hbar c^5} \left| P_{ab} \right|^2$$

This equation shows that the transition probability Au is in proportion to the cube of the angular frequency of the laser light $\omega_{\rm in}$.

FIG. A attached hereto illustrates the relationship between the wavelength λ and $\omega_{\rm m}^{-3}$. As shown in FIG. A, $\omega_{\rm m}^{-3}$ steeply changes in the short-wavelength region. Specifically, ω_{ba}^{3} at the wavelength of 405 nm (Sample 2A) is 10 % greater than was at the wavelength of 418 nm (Sample 2C). This means that A_{ab} of Sample 2A is about 10 % greater than As of Sample 2C. That is, an absorption saturation life of Sample 2A is about 10 % shorter than that of Sample C. The difference of about 10% is too large to neglect. As described above, Sample 2A uses light of a wavelength shorter than that of Sample 2C and has an absorption saturation life about 10 % shorter than that of Sample C. Generally, the transmittance of 2A should become smaller than that of 2C. However, Sample 2A has the same high transmittance of 16% as Sample 2C at 1MW/cm2. This high transmittance results from the fact that Sample 2A uses CdSe particles including an AMEO group covalently bonded thereto.

Next, Sample 2E of Table 2 is compared with Samples 2A and 2B of Table 2.

Sample 2E also uses CdSe particles including an AMEO group covalently bonded thereto. However, since R_{mod}/D_{Bohr} of Sample 2E is less than 0.25, Sample 2E has absorption saturation characteristics inferior to that of Sample 2A. In the meantime, the absorption saturation characteristics of Sample 2E is slightly superior to that of Sample 2B having similar R_{mod}/D_{Bohr} under the same wavelength λ , which proves the effect caused by CdSe particles including an AMEO group covalently bonded thereto.

DECLARATION

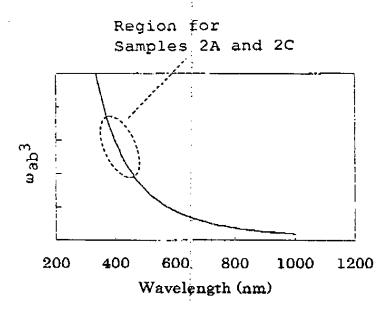
- 3 -

I, the undersigned, declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of this application or any patent issuing thereon.

Date april 23, 2004

Lange Todoni Kenji Todoni

From-PILLSBURY WINTHROP



FŢG. A

From-PILLSBURY WINTHROP

Table 2

Sample Semiconductor Particles M Amen Amen <th>_</th> <th></th> <th>Š</th> <th>er-reed]</th> <th>ntion 4</th> <th>F</th> <th></th> <th>Abso</th> <th>Absorption saturation</th> <th>ration</th>	_		Š	er-reed]	ntion 4	F		Abso	Absorption saturation	ration
Semiconductor Particles M Amax \(\) \(\)								ฮ	naracterist	ics
S R Dmod Dmod Dmod Dmod Dmod Dmod Dmod Dmod	Sample	Semicon	fuctor	particl	98				ī.	
CdSo, 1\$e0, 9 - 1.6nm 0.3 AMEO polymer 405nm 405nm 405nm 1 CdSo, 1\$e0, 9 - 1.0nm 0.21 PMAGA 410nm 400nm 1 CdSo, 1\$e0, 9 - 1.3nm 0.28 PMAGA 418nm 418nm 1 CdSo, 1\$e0, 9 - 6.5nm 1.32 PMAGA 640nm 640nm 1 CdSo, 6\$e0, 4 - 0.85nm 0.20 PMAGA 400nm 405nm 1		જ	p¢,	Dmod	Dmod/ DBohr	æ	Ашах	~	100kW/cm ² 1MW/cm ²	1MW/cm ²
CdSo.15e0.9 - 1.0mm 0.21 PMeGA 400nm 400nm 1 CdSo.18e0.9 - 1.3nm 0.28 PMeGA 418nm 418nm 1 CdSe - 6.5nm 1.32 PMeGA 640nm 640nm 1 CdSe 3.0mm 0.20 PMeGA 400nm 400nm 1 CdSo.6Seo.4 - 0.85nm 0.24 8iO2 405nm 405nm	2A	CdSe	AMEO		0.3	AMEO polymer	405rm	405nm	10%	168
CdSo.13e0.9 - 1.3nm 0.28 PMMGA 418nm 418nm 418nm 1 CdSe - 6.5nm 1.32 PMMGA 640nm 640nm 640nm 1 CdSe 1.0nm 0.20 PMMGA 400nm 400nm 405nm 1 CdSo.6SeO.4 - 0.85nm 0.24 8iO2 405nm 405nm 405nm	2B		_ 		12.0	ENDIG	400mm	400m	108	138
CdSo - 6.5nm 1.32 PMeGA 640nm 640nm 1.32 CdSo AMRO 1.0nm 0.20 PMeGA 400nm 400nm 1.0nm CdSo.6Seo.4 - 0.85nm 0.24 SiO2 405nm 405nm 405nm	2C		ß	1.3nm	0.28	PARCA	418nm	418nm	108	168
CdSo AMEO 1.0nm 0.20 PMeth 400nm 400nm 1 CdSo.65eo.4 - 0.85nm 0.24 SiO ₂ 405nm 405nm	2D	CdSe	1	6.5nm	1.32	Press	640mm	640mm	10%	138
CdS0.65e0.4 - 0.85nm 0.24 SiO2 405nm 405nm	2E	CdSe	OMNY	1.0mm	07'0	WHILE	400mm	400pm	104	348
	2F		-	0.85nm	92.0	Sio2	405nm	405nm	no change	ebus

 $D_{
m mod}/D_{
m Bohr}$ represents a ratio of model diameter $D_{
m mod}$ of semiconductor particles to Bohr radius DBohr of the semiconductor.